

NPN resistor-equipped transistors; R1 = 47 k Ω , R2 = 22 k Ω

PDTC144W series

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V _{CE0}	collector-emitter voltage	–	50	V
I _O	output current (DC)	–	100	mA
R1	bias resistor	47	–	k Ω
R2	bias resistor	22	–	k Ω

DESCRIPTION

NPN resistor-equipped transistor (see "Simplified outline, symbol and pinning" for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	PNP COMPLEMENT
	PHILIPS	EIAJ		
PDTC144WE	SOT416	SC-75	42	PDTA144WE
PDTC144WEF	SOT490	SC-89	34	PDTA144WEF
PDTC144WK	SOT346	SC-59	41	PDTA144WK
PDTC144WM	SOT883	SC-101	DD	PDTA144WM
PDTC144WS	SOT54 (TO-92)	SC-43	TC144W	PDTA144WS
PDTC144WT	SOT23	–	*20 ⁽¹⁾	PDTA144WT
PDTC144WU	SOT323	SC-70	*20 ⁽¹⁾	PDTA144WU

Note

1. * = p: Made in Hong Kong.
* = t: Made in Malaysia.
* = W: Made in China.

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SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTC144WS		1 2 3	base collector emitter
PDTC144WE PDTC144WEF PDTC144WK PDTC144WT PDTC144WU		1 2 3	base emitter collector
PDTC144WM		1 2 3	base emitter collector

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ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PDTC144WE	–	plastic surface mounted package; 3 leads	SOT416
PDTC144WEF	–	plastic surface mounted package; 3 leads	SOT490
PDTC144WK	–	plastic surface mounted package; 3 leads	SOT346
PDTC144WM	–	leadless ultra small plastic package; 3 solder lands; body 1.0 × 0.6 × 0.5 mm	SOT883
PDTC144WS	–	plastic single-ended leaded (through hole) package; 3 leads	SOT54
PDTC144WT	–	plastic surface mounted package; 3 leads	SOT23
PDTC144WU	–	plastic surface mounted package; 3 leads	SOT323

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CB0}	collector-base voltage	open emitter	–	50	V
V _{CE0}	collector-emitter voltage	open base	–	50	V
V _{EB0}	emitter-base voltage	open collector	–	10	V
V _i	input voltage		positive	+40	V
			negative	–10	V
I _O	output current (DC)		–	100	mA
I _{CM}	peak collector current		–	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
	SOT54	note 1	–	500	mW
	SOT23	note 1	–	250	mW
	SOT346	note 1	–	250	mW
	SOT323	note 1	–	200	mW
	SOT490	notes 1 and 2	–	250	mW
	SOT883	notes 2 and 3	–	250	mW
SOT416	note 1	–	150	mW	
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 μ m copper strip line.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W
SOT416	note 1	833	K/W	

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 μm copper strip line.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A	–	–	100	nA
I _{CEO}	collector-emitter cut-off current	V _{CE} = 30 V; I _B = 0 A	–	–	1	μA
		V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C	–	–	50	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A	–	–	110	μA
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 5 mA	60	–	–	
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	–	–	150	mV
V _{I(off)}	input-off voltage	I _C = 100 μA ; V _{CE} = 5 V	–	1.7	1.2	V
V _{I(on)}	input-on voltage	I _C = 2 mA; V _{CE} = 0.3 V	4	2.7	–	V
R1	input resistor		33	47	61	k Ω
$\frac{R2}{R1}$	resistor ratio		0.37	0.47	0.57	
C _c	collector capacitance	I _E = I _e = 0 A; V _{CB} = 10 V; f = 1 MHz	–	–	2.5	pF